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The invention relates to electrical measuring engineering, in particular to methods for producing environmental humidity change-resistant hydrogen sensors.

The method for producing a moisture-resistant hydrogen sensor comprises deposition of a nanostructured copper oxide film on a glass substrate by the method of chemical synthesis in solution, rapid heat treatment at 750°C for 60 s, deposition of an Al_2O_3 film by thermal evaporation in vacuum of aluminum triisopropylate $Al(C_3H_7O)_3$, heat treatment in air of the obtained structure at a temperature of 620°C for 40 min, and deposition of meander-shaped Cr-Au contacts.

Claims: 1
Fig.: 4